

IN THE CLAIMS

Please cancel claims 1-3 and 7, without prejudice or disclaimer.

Please rewrite claims 8, and 14, as follows:

1.-7. (Canceled).

8. (Currently Amended) ~~A semiconductor device according to claim 1,~~ A semiconductor device comprising: a main semiconductor device having on a circuit-formation surface a plurality of power supply line connection pads and a plurality of ground line connection pads, conductors each of which is electrically connected to either one of said power supply line connection pads or one of said ground line connection pads, respectively, and capacitors electrically connected to at least one surface of said conductors, wherein a flexible substrate comprising a metal foil ~~lead~~ leads, each of said metal foil leads serving as a one of said ~~conductor~~ conductors and an insulation layer provided at ~~least~~ least on a surface of each of said metal foil ~~lead,~~ leads, said surface of each of said metal foil leads opposing to said main semiconductor device, is joined to a said circuit-formation surface of said main semiconductor device.

9. (Original) A semiconductor device according to claim 8, wherein said insulation layer comprises a thermoplastic adhesive.

10. (Original) A semiconductor device according to claim 8, wherein said metal foil leads are formed on only a peripheral edge part of said circuit-formation surface of said main semiconductor device, a plurality of holes are provided on said insulation layer provided in a

region formed on said circuit-formation surface of said main semiconductor device, and in said region, no metal foil lead is provided, and at positions corresponding to said plurality of pads of said main semiconductor device, and a plurality of bumps of said main semiconductor device are caused to pass through each of said plurality of holes, thereby making joints to each of said plurality of pads.

11. – 13. (Canceled).

14. (Currently amended) A method for mounting a semiconductor device according to claim 10, comprising the steps of:

fabricating a main semiconductor device in which said power supply line connection pads and said ground line connection pads are alternately placed on and along a peripheral edge of said circuit-formation surface of a main semiconductor device, and in which bumps are formed over pads in regions other than said peripheral edge part of said circuit-formation surface;

fabricating a flexible substrate joining a capacitor between two neighboring metal foils foil leads;

fabricating said semiconductor device by making electrical connections between said power supply line connection pads and said ground line connection pads both being formed at a peripheral edge part of said main semiconductor device and said metal foil leads of said flexible substrate; and

mounting said semiconductor device onto said circuit board by placing said semiconductor device on said circuit board and heating it, so as to cause said bumps of said main semiconductor device to reflow.

15. (Original) A method for mounting a semiconductor device to a circuit board according to claim 14, whereby after mounting said semiconductor device to said circuit board, a resin is injected between a space between said semiconductor device and said circuit board.

16. – 19. (Canceled).

20. (Previously Added) A semiconductor device comprising:

a main semiconductor device having on a circuit-formation surface a plurality of power supply line connection pads and a plurality of ground line connection pads, conductors each of which is electrically connected to either one of said power supply connection pads or one of said ground line connection pads, respectively; and

capacitors electrically connected to at least one surface of said conductors; and

a flexible substrate comprising metal foil leads serving as said conductors and an insulation layer provided at least on a surface of said metal foil lead, said surface opposing said main semiconductor device, being joined to a circuit-formation surface of said main semiconductor device.

21. (Previously Added) A semiconductor device according to claim 1, wherein said conductor is a lead.

22. (Previously Added) A semiconductor device according to claim 1, wherein a plurality of first conductors are electrically connected to said power supply connection pads and a plurality of second conductors are electrically connected to said ground line connection pads; and

further wherein, said capacitors are electrically connected to one surface of said first conductor and connected to one surface of said second conductor.

23. (Previously Added) A semiconductor device according to claim 20, wherein said capacitors function as decoupling capacitors suppressing or compensating for a momentary drop in a DC voltage supplied to said main semiconductor device.

24. (Previously Added) A semiconductor device according to claim 20, wherein said power supply line connection pads and said ground line connection pads are alternately disposed along an edge extension direction of a peripheral edge of said circuit-formation surface of said main semiconductor device, and that said capacitor is connected between two neighboring conductors each connected respectively to a power supply line connection pad and a ground line connection pad.

25. (Previously Added) A semiconductor device according to claim 20, wherein either one of said power supply line connection pads or one of said ground line connection pads are connected to said conductor by a bump made of solder or gold.

26. (Previously Added) A semiconductor device according to claim 20, wherein said insulation layer comprises a thermoplastic adhesive.

27. (Previously Added) A semiconductor device according to claim 20, wherein said metal foil leads are formed on only a peripheral edge part of said circuit-formation surface of said main

semiconductor device, a plurality of holes are provided on said insulation layer provided in a region formed on said circuit-formation surface of said main semiconductor device, and in said region, no metal foil lead is provided, and at positions corresponding to said plurality of pads of said main semiconductor device, and a plurality of bumps of said main semiconductor device are caused to pass through each of said plurality of holes, thereby making joints to each of said plurality of pads.

28. (Previously Added) A semiconductor device according to claim 22, wherein said capacitors function as decoupling capacitors suppressing or compensating for a momentary drop in a DC voltage supplied to said main semiconductor device.

29. (Previously Added) A semiconductor device according to claim 22, wherein said power supply line connection pads and said ground line connection pads are alternately disposed along an edge extension direction of a peripheral edge of said circuit-formation surface of said main semiconductor device, and that said capacitor be provided connected between two neighboring conductors each connected respectively to a power supply line connection pad and a ground line connection pad.

30. (Previously Added) A semiconductor device according to claim 22, wherein either one of said power supply line connection pads or one of said ground line connection pads are connected to said conductor by a bump made of solder or gold.

31. (Previously Added) A semiconductor device according to claim 22, wherein a flexible substrate comprising a metal foil lead serving as a conductor and an insulation layer provided at least on a surface of said metal foil lead, said surface opposing said main semiconductor device, is joined to a circuit-formation surface of said main semiconductor device.

32. (Previously Added) A semiconductor device according to claim 22, wherein said insulation layer comprises a thermoplastic adhesive.

33. (Previously Added) A semiconductor device according to claim 22, wherein said metal foil leads are formed on only a peripheral edge part of said circuit-formation surface of said main semiconductor device, a plurality of holes are provided on said insulation layer provided in a region formed on said circuit-formation surface of said main semiconductor device, and in said region, no metal foil lead is provided, and at positions corresponding to said plurality of pads of said main semiconductor device, and a plurality of bumps of said main semiconductor device are caused to pass through each of said plurality of holes, thereby making joints to each of said plurality of pads.